Koichi Murata

List of Publications by Year
in descending order

26 papers	1,123 citations	1040056 9 h-index	642732 23 g-index
26 all docs	26 docs citations	26 times ranked	1962 citing authors

#	Article	IF	Citations
1	Limited current conduction due to various types of stacking faults in n-type 4H-SiC epilayers. Applied Physics Express, 2022, 15, 045502.	2.4	3
2	Carrier lifetime control by intentional boron doping in aluminum doped p-type 4H-SiC epilayers. Journal of Applied Physics, 2021, 129, .	2.5	6
3	Mechanical-stressing measurements of formation energy of single Shockley stacking faults in 4H-SiC. Applied Physics Express, 2021, 14, 044001.	2.4	6
4	Activation of two dopants, Bi and Er in Î´-doped layer in Si crystal. Nano Futures, 2021, 5, 045005.	2.2	0
5	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. Journal of Applied Physics, 2020, 128, 105702.	2.5	7
6	Fabrication of 4H-SiC PiN diodes on substrate grown by HTCVD method. Japanese Journal of Applied Physics, 2020, 59, SGGD07.	1.5	1
7	Direct nitridation of 4H-SiC(0001) surface by H2/N2 treatment. Applied Physics Express, 2020, 13, 095506.	2.4	1
8	Analysis of carrier lifetimes in Nâ€‰+â€‰B-doped n-type 4H-SiC epilayers. Journal of Applied Physics, 2019, 126, .	2.5	15
9	Wide-ranging control of carrier lifetimes in n-type 4H-SiC epilayer by intentional vanadium doping. Journal of Applied Physics, 2019, 126, .	2.5	21
10	Time-resolved photoluminescence spectral analysis of phonon-assisted DAP and e-A recombination in N+B-doped n-type 4H-SiC epilayers. Journal Physics D: Applied Physics, 2019, 52, 10LT01.	2.8	7
11	Control of Spin-Wave Damping in YIG Using Spin Currents from Topological Insulators. Physical Review Applied, 2019, 11, .	3.8	30
12	Suppressed expansion of single Shockley stacking faults at narrow widths in 4H-SiC. Applied Physics Express, 2019, 12, 124002.	2.4	9
13	Suppression of Bipolar Degradation in 4H-SiC Power Devices by Carrier Lifetime Control. , 2019, , .		2
14	Atomic characterization of nano-facet nitridation at SiC (1 1 Â¯ 00) surface. Applied Physics Letters, 2018, 112, 131603.	3.3	4
15	Atomic layer doping of Mn magnetic impurities from surface chains at a Ge/Si hetero-interface. Nanoscale, 2018, 10, 295-301.	5.6	4
16	Nanoengineering of an Si/MnGe quantum dot superlattice for high Curie-temperature ferromagnetism. Nanoscale, 2017, 9, 3086-3094.	5.6	13
17	Dopant activation mechanism of Bi wire-Î´-doping into Si crystal, investigated with wavelength dispersive fluorescence x-ray absorption fine structure and density functional theory. Journal of Physics Condensed Matter, 2017, 29, 155001.	1.8	3
18	Autosurfactant of the second kind: Bi enables Î´-doping of Bi in Si. Applied Physics Letters, 2017, 111, 152104.	3.3	1

#	Article	IF	Citations
19	Tailoring exchange couplings in magnetic topological-insulator/antiferromagnet heterostructures. Nature Materials, 2017, 16, 94-100.	27.5	137
20	Evidence for ferromagnetic coupling at the doped topological insulator/ferrimagnetic insulator interface. AIP Advances, 2016, 6, 055813.	1.3	8
21	Enhancing electric-field control of ferromagnetism through nanoscale engineering of high-Tc MnxGe1â^'x nanomesh. Nature Communications, 2016, 7, 12866.	12.8	35
22	Electric-field control of spinâ€“orbit torque in a magnetically doped topological insulator. Nature Nanotechnology, 2016, 11, 352-359.	31.5	212
23	Metal-to-insulator switching in quantum anomalous Hall states. Nature Communications, 2015, 6, 8474.	12.8	136
24	Scale-Invariant Quantum Anomalous Hall Effect in Magnetic Topological Insulators beyond the Two-Dimensional Limit. Physical Review Letters, 2014, 113, 137201.	7.8	453
25	Hybrid Laser Activation of Highly Concentrated Bi Donors in Wire-Î´-Doped Silicon. Applied Physics Express, 2010, 3, 061302.	2.4	9
26	Peak Effect as Precursor to Lock-in State in Bi2Sr2CaCu2O8+Î´ Single Crystal. AIP Conference Proceedings, 2006, , .	0.4	0